

L Number	Hits	Search Text	DB	Time stamp
1	273	(gate with germanium) same \$4silicon same nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/03 17:43
2	87	((gate with germanium) same \$4silicon same nitride) and (@ad<19990623 or @rlad<19990623)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/03 17:43
3	3	((polysilicon with over with germanium with gate) same nitride) and (@ad<19990623 or @rlad<19990623)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/03 17:41
4	2	((polysilicon with top with germanium with gate) same nitride) and (@ad<19990623 or @rlad<19990623)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/03 17:41
5	76	((gate with germanium) same \$4silicon same nitride) and (@ad<19990623 or @rlad<19990623)) and dop\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/03 17:43
6	99	(gate with germanium) same \$4silicon same nitride same dop\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/03 17:43
7	32	((gate with germanium) same \$4silicon same nitride same dop\$3) and (@ad<19990623 or @rlad<19990623)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/03 17:43
-	212	(gate adj1 electrode) with germanium	USPAT; EPO; JPO; DERWENT	2004/03/03 16:16
-	2	((gate adj1 electrode) with germanium) same (conduct\$3 adj1 film)	USPAT; EPO; JPO; DERWENT	2002/01/23 10:26
-	13	((gate adj1 electrode) with germanium) and (conduct\$3 adj1 film)	USPAT; EPO; JPO; DERWENT	2002/01/23 10:26
-	9	((gate adj1 electrode) with germanium) same (p-type near3 dop\$3)	USPAT; EPO; JPO; DERWENT	2002/01/23 16:26
-	2	((gate adj1 electrode) with germanium) same (silicon adj1 substrate) same MOSFET	USPAT; EPO; JPO; DERWENT	2002/01/24 08:55
-	31	((gate adj1 electrode) with germanium) and (silicon adj1 substrate) and MOSFET	USPAT; EPO; JPO; DERWENT	2002/01/24 10:23
-	11	"5216271"	USPAT; EPO; JPO; DERWENT	2002/01/31 13:12
-	8	"5101247"	USPAT; EPO; JPO; DERWENT	2002/01/31 13:49
-	2511	conduct\$3 with (transition near3 metal)	USPAT; JPO; DERWENT	2002/01/31 15:42
-	0	(conduct\$3 with (transition near3 metal)) and (gate near4 germanium)	USPAT; JPO; DERWENT	2002/01/31 15:38
-	9	(conduct\$3 with (transition near3 metal)) and gate and germanium	USPAT; JPO; DERWENT	2002/01/31 15:24
-	0	(conduct\$3 with (transition near3 metal)) same (gate and germanium)	USPAT; JPO; DERWENT	2002/01/31 15:40
-	104	(conduct\$3 with (transition near3 metal)) and (metal near2 silicide)	USPAT; JPO; DERWENT	2002/01/31 15:40
-	407	(conduct\$3 near3 (film or layer)) with (transition near3 metal)	USPAT; JPO; DERWENT	2002/01/31 15:59

-	931	(germanium near2 (film or layer)) and (conduct\$3 near2 (film or layer))	USPAT; JPO; DERWENT	2002/02/01 10:33
-	35609	(polysilicon near2 (layer or film))	USPAT; JPO; DERWENT	2002/02/01 10:27
-	150	((polysilicon near2 (layer or film))) and ((germanium near2 (film or layer)) and (conduct\$3 near2 (film or layer)))	USPAT; JPO; DERWENT	2002/02/01 10:31
-	0	"polysilicon layer between a germanium layer and a conductive layer"	USPAT; JPO; DERWENT	2002/02/01 10:33
-	158	(germanium near2 (film or layer)) with (conduct\$3 near2 (film or layer))	USPAT; JPO; DERWENT	2002/02/01 11:18
-	11	((germanium near2 (film or layer)) with (conduct\$3 near2 (film or layer))) with (polysilicon near2 (layer or film))	USPAT; JPO; DERWENT	2002/02/01 10:36
-	6	((germanium near2 (film or layer)) with (conduct\$3 near2 (film or layer))) with silicide	USPAT; JPO; DERWENT	2002/02/01 11:00
-	1676	(germanium near2 (film or layer)) with (\$4silicon near2 (film or layer))	USPAT; JPO; DERWENT	2002/02/01 11:23
-	35	((germanium near2 (film or layer)) with (\$4silicon near2 (film or layer))) with silicide	USPAT; JPO; DERWENT	2002/02/01 11:23
-	12	"5608249"	USPAT; JPO; DERWENT	2002/02/01 14:09
-	83	(gate adj (dielectric or insulator)) with (germanium or ge)	USPAT; EPO; JPO; DERWENT	2002/09/15 19:03
-	67	((gate adj (dielectric or insulator)) with (germanium or ge)) and @ad<19992306	USPAT; EPO; JPO; DERWENT	2002/09/15 19:05
-	58	((gate adj (dielectric or insulator)) with (germanium or ge)) and @ad<19990623	USPAT; EPO; JPO; DERWENT	2002/09/22 09:08
-	18	((germanium or ge) adj (film or layer)) with (gate adj insulat\$3)	USPAT; EPO; JPO; DERWENT	2002/09/19 15:59
-	16	((((germanium or ge) adj (film or layer)) with (gate adj insulat\$3)) and @ad<19990623	USPAT; EPO; JPO; DERWENT	2002/09/19 16:00
-	19	((((gate adj electrode) with (germanium or ge)) and @ad<19990623) and ((gate adj (insulator or dielectric)) with (germanium or ge))	USPAT; EPO; JPO; DERWENT	2002/09/22 09:11
-	382	((gate adj electrode) with (germanium or ge)) and @ad<19990623	USPAT; EPO; JPO; DERWENT	2002/09/22 09:27
-	157	((gate adj1 electrode) with (germanium or ge)) same (gate adj (dielectric or insulat\$3 or \$2oxide)) and (dop\$3 same ("p-type" or boron or b or al or aluminum or ga or in))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 14:01
-	44	((((gate adj1 electrode) with (germanium or ge)) same (gate adj (dielectric or insulat\$3 or \$2oxide)) and (dop\$3 same ("p-type" or boron or b or al or aluminum or ga or in))) and @ad<19990623	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 15:30
-	0	(germanium near3 gate) same "1.times.10.sup.\$2"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 15:21
-	3	(germanium near3 gate) same ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 15:25

-	3	(germanium with gate with electrode) same ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 16:00
-	20	(germanium with film) same "p-type" same impurities same dop\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 15:29
-	15	((germanium with film) same "p-type" same impurities same dop\$3) and @ad<19990623	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 16:00
-	44	(germanium with film) same ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 16:13
-	19	((germanium with film) same ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20")) and @ad<19990623	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 16:12
-	701	(ge or germanium) with "above" with oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 16:12
-	519	((ge or germanium) with "above" with oxide) and @ad<19990623	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 17:00
-	7	((ge or germanium) with "above" with oxide) and @ad<19990623) and ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 17:08
-	13	((ge or germanium) with "above" with oxide) and @ad<19990623) and (gate adj (dielectric or oxide or insulat\$3)) and (gate adj electrode) and "p-type"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 16:58
-	0	(germanium adj gate adj electrode) with "on" with (insulat\$3 or oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 17:00
-	27	germanium adj gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 17:00
-	3	(germanium adj gate adj electrode) and @ad<19990623	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 17:17
-	45	((ge or germanium) with electrode) same ("p-type" or boron) same ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 17:18
-	33	((ge or germanium) with electrode) same ("p-type" or boron) same ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20")) and @ad<19990623	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 17:40
-	3	((ge or germanium) with electrode with gate) same ("p-type" or boron) same ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 17:31

-	5	((ge or germanium) with gate) same ("p-type" or boron) same ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 17:34
-	2	(germanium same (metal adj silicide) same polysilicon same (gate adj electrode)) and @ad<19990623	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 17:42
-	36	(germanium same (metal adj silicide) same polysilicon) and @ad<19990623	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 18:03
-	50	(germanium with (work adj function)) same (silicon with (work adj function))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 18:13
-	17	germanium with (work adj function) with "ev"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 18:14
-	283	((gate adj1 electrode) with (germanium or ge)) same ("p-type" or b or boron or aluminum or indium or gallium)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 17:49
-	41	((((gate adj1 electrode) with (germanium or ge)) same ("p-type" or b or boron or aluminum or indium or gallium)) and ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20"))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 17:50
-	20	((((gate adj1 electrode) with (germanium or ge)) same ("p-type" or b or boron or aluminum or indium or gallium)) and ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20")) and @ad<19990623	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 18:21
-	814	(gate adj1 electrode) with (germanium or ge)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 17:49
-	8	((gate adj1 electrode) with (germanium or ge)) same ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 17:55
-	2	("5952701" "6262456" "2002/0113294").PN.	USPAT	2003/08/13 17:52
-	2	(work adj function) same (germanium or ge) same (mid with gap with energy with silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 18:19
-	0	1111686.URPN.	USPAT	2003/08/13 18:05
-	5	("4984043" "4990974" "5194923" "5250818" "5619057").PN.	USPAT	2003/08/13 18:05
-	39	(boron or b) with implant\$5 with (germanium or ge) with "kev"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 18:20
-	20	((boron or b) with implant\$5 with (germanium or ge) with "kev") and @ad<19990623	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 18:21
-	31	(dop\$3 or implant\$5) with (germanium or ge) with (gate adj electrode) with (boron or b)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 18:46

-	13	((dop\$3 or implant\$5) with (germanium or ge) with (gate adj electrode) with (boron or b)) and @ad<19990623	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 18:46
-	0	jp-27854-\$.did	USPAT; EPO; JPO; DERWENT	2003/08/22 11:24
-	0	jp-1027854-\$.did	USPAT; EPO; JPO; DERWENT	2004/02/19 11:57
-	0	jp-027854-\$.did	USPAT; EPO; JPO; DERWENT	2004/02/19 11:57
-	0	jp-027854-\$.did.	USPAT; EPO; JPO; DERWENT	2004/02/19 11:58
-	2	jp-10027854-\$.did.	USPAT; EPO; JPO; DERWENT	2004/02/19 11:58